## DSSEETS . 11555

## ABSTRACT OF THE DISCLOSURE

Reliable Cu interconnects are formed by filling an opening in a dielectric layer with Cu and then laser thermal annealing in NH<sub>3</sub> to reduce copper oxide and to reflow the deposited Cu, thereby eliminating voids and reducing contact resistance. Embodiments include laser thermal annealing employing an NH<sub>3</sub> flow rate of about 200 to about 2,000 sccn.